

**SEMICONDUCTOR  
TECHNICAL DATA**

**KDS115**  
SILICON EPITAXIAL TYPE DIODE

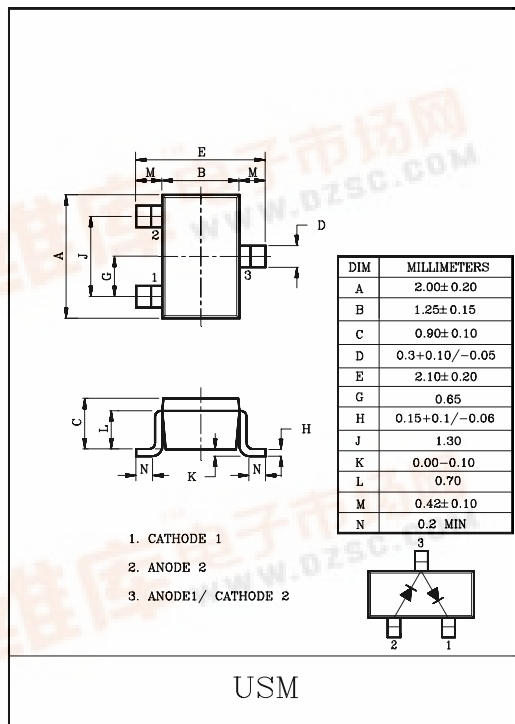
VHF TUNER BAND SWITCH APPLICATIONS.

FEATURES

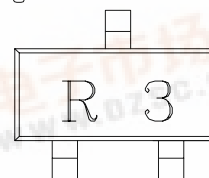
- Small Package.
- Small Total Capacitance :  $C_T=1.2\text{pF(Max.)}$ .
- Low Series Resistance :  $r_s=0.6\Omega(\text{Typ.})$ .

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	50	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ\text{C}$



Marking



ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F$	$I_F=2\text{mA}$	-	-	0.85	V
Reverse Current	$I_R$	$V_R=15\text{V}$	-	-	0.1	$\mu\text{A}$
Reverse Voltage	$V_R$	$I_R=1\mu\text{A}$	30	-	-	V
Total Capacitance	$C_T$	$V_R=6\text{V}, f=1\text{MHz}$	-	0.8	1.2	pF
Series Resistance	$r_s$	$I_F=2\text{mA}, f=100\text{MHz}$	-	0.6	0.9	$\Omega$

# KDS115

